

DEVICE FOR DEEP PURIFICATION OF Ga, In, AND Pb

Areas of Application

The device is used to synthesize microelectronic and optoelectronic materials

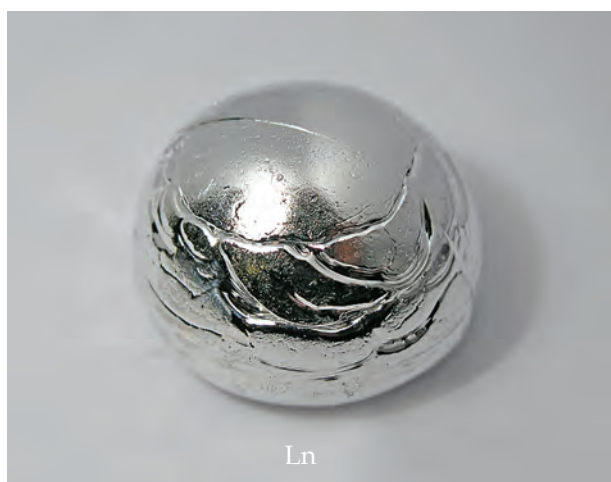
Specification

Weight of original charge, kg	2.3
Product yield, % of original charge	90
Yield capacity, g/hour	300–400
Operating temperature, °C	950–1300
Fineness, %	99.9–99.99... >99.999–99.9999



Advantages

The equipment is unique in Ukraine.
Deep purification from a wide range of impurities;
high efficiency of refining process;
high product yield

Stage of Development.
Suggestions for Commercialization

IRL6, TRL6
Pure metals manufactured, upon request



IPR Protection

IPR3

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